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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known Application Number: <u>TBA 10/617737</u> Filing Date: <u>Herewith</u> First Named Inventor: <u>Takashi OHSAWA</u> Group Art Unit: <u>Unknown 2815</u> Examiner Name: <u>Unknown A. Wilson</u> Attorney Docket Number: <u>002372.00045</u>	
Sheet	1	of	1

U.S. PATENT DOCUMENTS						
Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₂
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<u>one</u>		G. VINCENT, et al., "Electric field effect on the thermal emission of traps in semiconductor junctions", 1979 American Institute of Physics, pp. 5484-5487	
		J. LEISS, et al., "dRAM Design Using the Taper-Isolated Dynamic RAM Cell", IEEE Transactions on Electron Devices, Vol. ED-29, No. 4, April 1982, pp. 707-714	
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		H. WANN, et al., "A Capacitorless DRAM Cell on SOI Substrate", 1993 IEEE, pp. 635-638	
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Examiner Signature	<u>A. Wilson</u>	Date Considered	<u>9/2/04</u>
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